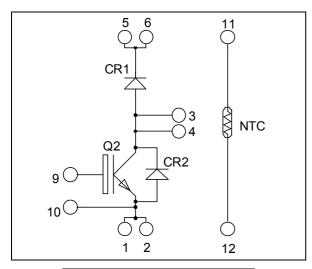
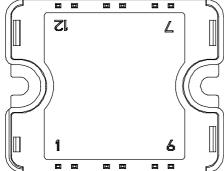


# Boost chopper NPT IGBT Power Module

$$V_{CES} = 1200V$$
  
 $I_{C} = 50A$  @  $Tc = 80$ °C





Pins 1/2; 3/4; 5/6 must be shorted together

#### **Application**

- AC and DC motor control
- Switched Mode Power Supplies
- Power Factor Correction

#### **Features**

- Non Punch Through (NPT) Fast IGBT
  - Low voltage drop
  - Low tail current
  - Switching frequency up to 50 kHz
  - Soft recovery parallel diodes
  - Low diode VF
  - Low leakage current
  - RBSOA and SCSOA rated
- Very low stray inductance
- Internal thermistor for temperature monitoring
- High level of integration

#### Benefits

- Outstanding performance at high frequency operation
- Direct mounting to heatsink (isolated package)
- Low junction to case thermal resistance
- Solderable terminals both for power and signal for easy PCB mounting
- Low profile
- **RoHS Compliant**

### Absolute maximum ratings

Symbol	Parameter		Max ratings	Unit
$V_{CES}$	Collector - Emitter Breakdown Voltage		1200	V
Ţ	Continuous Collector Current	$T_c = 25^{\circ}C$	75	
$I_{C}$	Continuous Conector Current	$T_c = 80$ °C	50	Α
$I_{CM}$	Pulsed Collector Current	$T_c = 25^{\circ}C$	150	
$V_{GE}$	Gate – Emitter Voltage		±20	V
$P_{D}$	Maximum Power Dissipation	$T_c = 25^{\circ}C$	312	W
RBSOA	Reverse Bias Safe Operating Area	$T_i = 150^{\circ}C$	100A @ 1200V	

These Devices are sensitive to Electrostatic Discharge. Proper Handling Procedures Should Be Followed. See application note APT0502 on www.microsemi.com



### All ratings @ $T_j = 25$ °C unless otherwise specified

### **Electrical Characteristics**

 Symbol	Characteristic	Test Conditions		Min	Тур	Max	Unit
$I_{CES}$	Zero Gate Voltage Collector Current	$V_{GE} = 0V$	$T_i = 25^{\circ}C$			250	μA
1CES	Zero Gate voltage Collector Current	$V_{CE} = 1200V$	$T_{i} = 125^{\circ}C$			500	μΛ
17	Callantan Frankton antonotica Valtana	$V_{GE} = 15V$	$T_j = 25$ °C		3.2	3.7	V
$V_{CE(sat)}$	Collector Emitter saturation Voltage	$I_C = 50A$	$T_j = 125$ °C		4.0		V
$V_{GE(th)}$	Gate Threshold Voltage	$V_{GE} = V_{CE}$ , $I_C = 1 \text{ mA}$		4.5		6.5	V
$I_{GES}$	Gate – Emitter Leakage Current	$V_{GE} = 20 \text{ V}, V_{CE} = 0 \text{ V}$				100	nA

**Dynamic Characteristics** 

·	Characteristic	Test Conditions	ı	Min	Тур	Max	Unit
C <sub>ies</sub>	Input Capacitance	$V_{GE} = 0V$			3450		
$C_{oes}$	Output Capacitance	$V_{CE} = 25V$			330		pF
$C_{res}$	Reverse Transfer Capacitance	f = 1MHz			220		
$Q_{\mathrm{g}}$	Total gate Charge	$V_{GS} = 15V$			330		nC
$Q_{ge}$	Gate – Emitter Charge	$V_{Bus} = 600V$			35		
$Q_{gc}$	Gate – Collector Charge	$I_C = 50A$			200		
T <sub>d(on)</sub>	Turn-on Delay Time	Inductive Switching (25°C) $V_{GE} = 15V$ $V_{Bus} = 600V$ $I_{C} = 50A$ $R_{G} = 5 \Omega$			35		ns
$T_{r}$	Rise Time				65		
$T_{d(off)}$	Turn-off Delay Time				320		
$T_{\mathrm{f}}$	Fall Time				30		
T <sub>d(on)</sub>	Turn-on Delay Time	Inductive Switching (125°C) $V_{GE} = \pm 15V$ $V_{Bus} = 600V$ $I_{C} = 50A$ $R_{G} = 5 \Omega$			35		- ns
$T_{\rm r}$	Rise Time				65		
$T_{d(off)}$	Turn-off Delay Time				360		
$T_{\rm f}$	Fall Time				40		
Eon	Turn-on Switching Energy	$V_{GE} = \pm 15V$ $V_{Bus} = 600V$	$T_j = 125$ °C		6.9		mI
$E_{\text{off}}$	Turn-off Switching Energy	$I_{C} = 50A$ $R_{G} = 5 \Omega$	$T_j = 125$ °C		3.05		mJ

**Chopper diode ratings and characteristics** 

Symbol	Characteristic		Test Conditions		Тур	Max	Unit
$V_{RRM}$	Maximum Peak Repetitive Reverse Voltage			1200			V
T	Maximum Reverse Leakage Current $V_R=1200V$ -	V -1200V	$T_j = 25$ °C			100	^
1 <sub>RM</sub>		$T_{j} = 125^{\circ}C$			500	μA	
$I_F$	DC Forward Current		$Tc = 80^{\circ}C$		60		A
	Diode Forward Voltage	$I_F = 60A$			2.5	3	
$V_{\mathrm{F}}$		$I_F = 120A$			3		V
		$I_F = 60A$	$T_{j} = 125^{\circ}C$		1.8		
t	Reverse Recovery Time	$I_F = 60A$ $V_R = 800V$	$T_j = 25$ °C		265		ns
$t_{rr}$			$T_{j} = 125^{\circ}C$		350		113
Q <sub>rr</sub>	Reverse Recovery Charge	$di/dt = 200 \text{ A/}\mu\text{s}$	$T_j = 25$ °C		560		nC
			$T_{j} = 125^{\circ}C$		2890		IIC



### Thermal and package characteristics

Symbol	Characteristic			Min	Тур	Max	Unit
$R_{thJC}$	Junction to Case Thermal Resistance		IGBT			0.4	°C/W
KthJC		Diode			0.9	C/W	
$V_{ISOL}$	RMS Isolation Voltage, any terminal to case t =1 min, 50/60Hz			4000			V
$T_{J}$	Operating junction temperature range			-40		150	
$T_{STG}$	Storage Temperature Range			-40		125	°C
$T_{\rm C}$	Operating Case Temperature	-40		100			
Torque	Mounting torque	To heatsin	ık M4	2		3	N.m
Wt	Package Weight					80	g

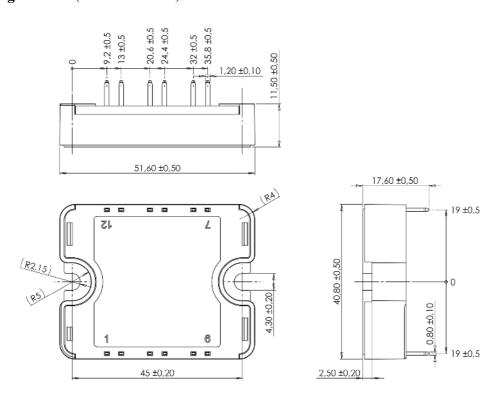
Temperature sensor NTC (see application note APT0406 on www.microsemi.com for more information).

Symbol	Characteristic	Min	Typ	Max	Unit
R <sub>25</sub>	Resistance @ 25°C		50		kΩ
B 25/85	$T_{25} = 298.15 \text{ K}$		3952		K

$$R_T = \frac{R_{25}}{\exp \left[ B_{25/85} \left( \frac{1}{T_{25}} - \frac{1}{T} \right) \right]} \quad \text{T: Thermistor temperature}$$

$$R_T: \text{ Thermistor value at T}$$

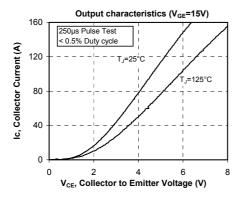
### SP1 Package outline (dimensions in mm)

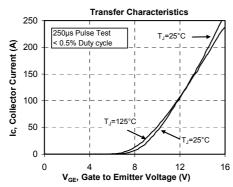


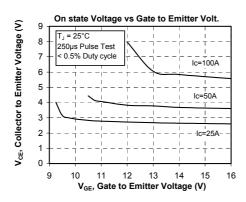
See application note 1904 - Mounting Instructions for SP1 Power Modules on www.microsemi.com

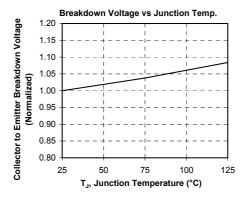


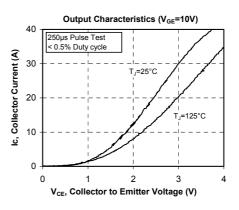
### **Typical Performance Curve**

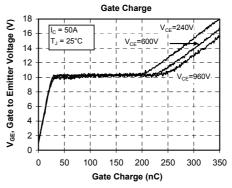


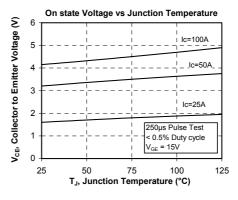


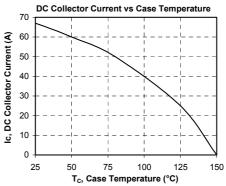




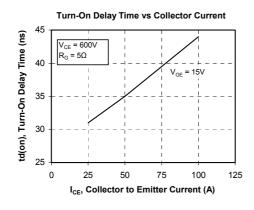


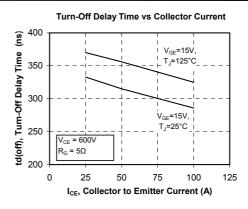


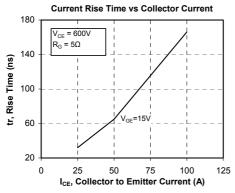


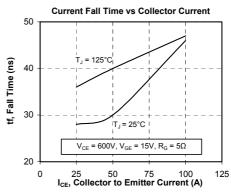


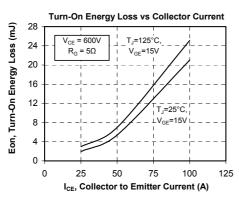


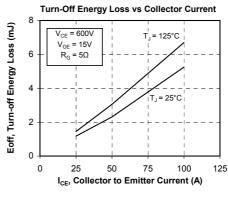


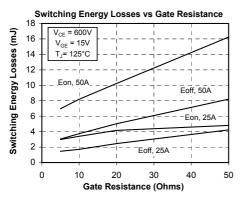


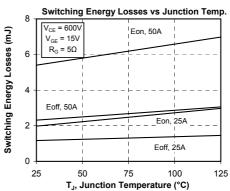




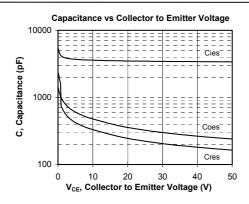


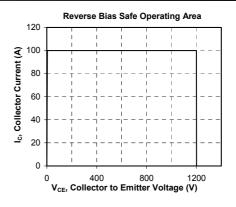


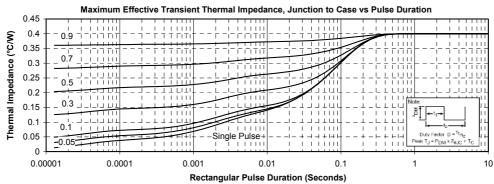


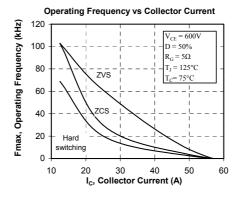












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